

Mladen Petravac

List of Publications by Year in descending order

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146
papers

2,525
citations

257429

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265191

42
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147
all docs

147
docs citations

147
times ranked

2964
citing authors

#	ARTICLE	IF	CITATIONS
1	Large-scale mechanical peeling of boron nitride nanosheets by low-energy ball milling. Journal of Materials Chemistry, 2011, 21, 11862.	6.7	373
2	Disorder in ball-milled graphite revealed by Raman spectroscopy. Carbon, 2013, 57, 515-519.	10.3	158
3	Gettering of copper to hydrogen-induced cavities in silicon. Applied Physics Letters, 1995, 66, 1231-1233.	3.3	123
4	Decoration of nitrogen vacancies by oxygen atoms in boron nitride nanotubes. Physical Chemistry Chemical Physics, 2010, 12, 15349.	2.8	79
5	Isotopically Enriched 10BN Nanotubes. Advanced Materials, 2006, 18, 2157-2160.	21.0	51
6	Chemical states of nitrogen in ZnO studied by near-edge X-ray absorption fine structure and core-level photoemission spectroscopies. Surface Science, 2006, 600, L81-L85.	1.9	49
7	Mechanically activated catalyst mixing for high-yield boron nitride nanotube growth. Nanoscale Research Letters, 2012, 7, 417.	5.7	49
8	Surface near-edge x-ray adsorption fine structure of hydrogenated diamond films and Di(100) surfaces studied by H ⁺ and H ⁺ ion desorption. Applied Physics Letters, 1998, 73, 1152-1154.	3.3	41
9	Using doping superlattices to study transient-enhanced diffusion of boron in regrown silicon. Applied Physics Letters, 1996, 68, 3111-3113.	3.3	40
10	Photon-stimulated desorption of H ⁺ and H ⁺ ions from diamond surfaces: Evidence for direct and indirect processes. Physical Review B, 1999, 59, 3203-3209.	3.2	40
11	Formation of defects in boron nitride by low energy ion bombardment. Journal of Applied Physics, 2009, 106, .	2.5	39
12	Oxidation of silicon by low energy oxygen bombardment. Journal of Applied Physics, 1994, 76, 1840-1846.	2.5	38
13	MeV implantation into semiconductors. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 507-513.	1.4	33
14	On the estimation of depth resolution during sputter profiling. Applied Physics Letters, 1993, 62, 278-280.	3.3	33
15	Core-level photoemission and near-edge x-ray absorption fine-structure studies of GaN surface under low-energy ion bombardment. Journal of Applied Physics, 2004, 95, 5487-5493.	2.5	32
16	Biomass bottom ash & dolomite similarly ameliorate an acidic low-nutrient soil, improve phytonutrition and growth, but increase Cd accumulation in radish. Science of the Total Environment, 2021, 753, 141902.	8.0	32
17	Functionalization of biodegradable magnesium alloy implants with alkylphosphonate self-assembled films. Materials Science and Engineering C, 2013, 33, 2152-2158.	7.3	30
18	Controlling the grain size of polycrystalline TiO ₂ films grown by atomic layer deposition. Applied Surface Science, 2017, 419, 564-572.	6.1	30

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19	Nanosize diamond formation promoted by direct current glow discharge process: Synchrotron radiation and high resolution electron microscopy studies. <i>Applied Physics Letters</i> , 1998, 72, 2517-2519.	3.3	29
20	Interaction of defects and metals with nanocavities in silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2001, 178, 33-43.	1.4	29
21	Silane Flow Rate Dependence of SiO _x Cap Layer Induced Impurity-Free Intermixing of GaAs/AlGaAs Quantum Wells. <i>Journal of the Electrochemical Society</i> , 2000, 147, 1950.	2.9	28
22	The potential-assisted deposition as valuable tool for producing functional apatite coatings on metallic materials. <i>Electrochimica Acta</i> , 2014, 127, 173-179.	5.2	26
23	The role of oxygen on the stability of gettering of metals to cavities in silicon. <i>Applied Physics Letters</i> , 1999, 75, 2424-2426.	3.3	25
24	New insights into the mechanism of pseudocapacitance deterioration in electrodeposited MnO ₂ under negative potentials. <i>Journal of Power Sources</i> , 2013, 240, 252-257.	7.8	25
25	High dose, heavy ion implantation into metals: The use of a sacrificial carbon surface layer for increased dose retention. <i>Journal of Applied Physics</i> , 1992, 72, 4014-4019.	2.5	24
26	Broadening of vibrational levels in X-ray absorption spectroscopy of molecular nitrogen in compound semiconductors. <i>Chemical Physics Letters</i> , 2006, 425, 262-266.	2.6	24
27	Novel, oxygenated clinoptilolite material efficiently removes aluminium from aluminium chloride-intoxicated rats in vivo. <i>Microporous and Mesoporous Materials</i> , 2017, 249, 146-156.	4.4	23
28	Anodic-oxide-induced intermixing in GaAs-AlGaAs quantum-well and quantum-wire structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1998, 4, 629-635.	2.9	22
29	Surface Modification of Biodegradable Magnesium Alloys. <i>Journal of the Electrochemical Society</i> , 2012, 159, C253-C258.	2.9	22
30	Gettering of platinum and silver to cavities formed by hydrogen implantation in silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1997, 127-128, 297-300.	1.4	21
31	Potential Assisted Formation and Characterization of Hydroxyapatite Coatings on Biodegradable Magnesium Alloys. <i>Journal of the Electrochemical Society</i> , 2013, 160, H674-H680.	2.9	21
32	Omniphobic Etched Aluminum Surfaces with Anti-Icing Ability. <i>Langmuir</i> , 2020, 36, 10916-10922.	3.5	21
33	GaAs delta-doped layers in Si for evaluation of SIMS depth resolution GaAs. <i>Surface and Interface Analysis</i> , 2000, 29, 362-368.	1.8	20
34	NEXAFS and XPS study of GaN formation on ion-bombarded GaAs surfaces. <i>Vacuum</i> , 2009, 84, 41-44.	3.5	20
35	Oxidation of nickel surfaces by low energy ion bombardment. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2016, 371, 286-289.	1.4	20
36	Grain size effect on photocatalytic activity of TiO ₂ thin films grown by atomic layer deposition. <i>Thin Solid Films</i> , 2020, 709, 138215.	1.8	18

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37	The electronic structure of the $\text{Ni}(\text{OH})_2$ films: Influence on the production of the high-performance Ni catalyst surface. <i>Journal of Power Sources</i> , 2015, 282, 421-428.	7.8	17
38	Ultrathin Hybrid SiAlCOH Dielectric Films through Ring-Opening Molecular Layer Deposition of Cyclic Tetrasiloxane. <i>Chemistry of Materials</i> , 2021, 33, 1022-1030.	6.7	17
39	Enhancement of stability of Prussian blue thin films by electrochemical insertion of Ni^{2+} ions: A stable electrocatalytic sensing of H_2O_2 in mild alkaline media. <i>Electrochimica Acta</i> , 2012, 78, 452-458.	5.2	16
40	Oxide formation on chromium metal surfaces by low-energy oxygen implantation at room temperature. <i>Thin Solid Films</i> , 2017, 636, 225-231.	1.8	16
41	The influence of cavities and point defects on boron diffusion in silicon. <i>Applied Physics Letters</i> , 1998, 72, 2418-2420.	3.3	15
42	Compositional changes on GaN surfaces under low-energy ion bombardment studied by synchrotron-based spectroscopies. <i>Applied Physics Letters</i> , 2003, 83, 4948-4950.	3.3	15
43	Direct observation of defect levels in hexagonal BN by soft X-ray absorption spectroscopy. <i>Chemical Physics Letters</i> , 2009, 472, 190-193.	2.6	15
44	High-resolution x-ray absorption studies of core excitons in hexagonal boron nitride. <i>Applied Physics Letters</i> , 2012, 101, 191604.	3.3	15
45	Residual chlorine in TiO_2 films grown at low temperatures by plasma enhanced atomic layer deposition. <i>Thin Solid Films</i> , 2017, 628, 142-147.	1.8	15
46	Low temperature AC susceptibility of yttrium barium copper oxide single crystals: Attempts to measure the superconducting penetration depth. <i>Physica C: Superconductivity and Its Applications</i> , 1988, 153-155, 1491-1492.	1.2	14
47	Conductivity in insulators due to implantation of conducting species. <i>Journal of Applied Physics</i> , 1993, 73, 3841-3845.	2.5	14
48	Segregation effects in SIMS profiling of impurities in silicon by low energy oxygen ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1996, 118, 151-155.	1.4	14
49	Efficient gettering of low concentrations of copper contamination to hydrogen induced nanocavities in silicon. <i>Applied Physics Letters</i> , 1998, 73, 2639-2641.	3.3	14
50	Angular and energy dependence of the ion beam oxidation of Si using oxygen ions from a duoplasmatron source. <i>Surface and Interface Analysis</i> , 1999, 27, 92-97.	1.8	14
51	Defect acceptor and donor in ion-bombarded GaN. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005, 23, 1340-1345.	2.1	14
52	Characterization of molecular nitrogen in III-V compound semiconductors by near-edge x-ray absorption fine structure and photoemission spectroscopies. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 592-596.	2.1	14
53	Oxidation of Cobalt by Oxygen Bombardment at Room Temperature. <i>Journal of Physical Chemistry C</i> , 2016, 120, 22421-22425.	3.1	14
54	Semiconducting Properties of the Oxide Films Formed on Tin: Capacitive and XPS Studies. <i>Journal of the Electrochemical Society</i> , 2016, 163, C221-C227.	2.9	14

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55	Preparation of non-oxidized Ge quantum dot lattices in amorphous Al ₂ O ₃ , Si ₃ N ₄ and SiC matrices. Nanotechnology, 2019, 30, 335601.	2.6	14
56	Formation of oxides on CoCrMo surfaces at room temperature: An XPS study. Applied Surface Science, 2019, 471, 475-481.	6.1	14
57	Role of Hydrogen-Related Defects in Photocatalytic Activity of ZnO Films Grown by Atomic Layer Deposition. Journal of Physical Chemistry C, 2020, 124, 8861-8868.	3.1	14
58	Electronic effects in ion-stimulated desorption of positive halogen ions from semiconductor surfaces. Nuclear Instruments & Methods in Physics Research B, 1995, 101, 64-68.	1.4	13
59	Resonantlike desorption of negative ions by core-level excitation under electron bombardment. Physical Review B, 1996, 53, R4257-R4259.	3.2	13
60	Microstructural difference between platinum and silver trapped in hydrogen induced cavities in silicon. Applied Physics Letters, 1998, 72, 2713-2715.	3.3	13
61	Direct observation of defects in hexagonal boron nitride by near-edge X-ray absorption fine structure and X-ray photoemission spectroscopy. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 619, 94-97.	1.6	13
62	Phase transformations and compound formation during ion irradiation of materials. Nuclear Instruments & Methods in Physics Research B, 1994, 84, 199-203.	1.4	12
63	Segregation effects of Li, K, and F in Si during depth profiling by oxygen ions. Journal of Applied Physics, 2000, 87, 2178-2184.	2.5	12
64	Selectivity of nanocavities and dislocations for gettering of Cu and Fe in silicon. Applied Physics Letters, 2001, 78, 2682-2684.	3.3	12
65	Large enhancement of photocatalytic activity in ZnO thin films grown by plasma-enhanced atomic layer deposition. Surfaces and Interfaces, 2021, 23, 100984.	3.0	12
66	Ion-induced noncollisional ejection of positive secondary ions. Surface Science, 1991, 259, 215-220.	1.9	11
67	Very high carbon δ -doping concentration in Al _x Ga _{1-x} As grown by metalorganic vapor phase epitaxy using trimethylaluminum as a doping precursor. Journal of Applied Physics, 1996, 79, 3554-3559.	2.5	11
68	High-resolution photoemission study of hydrogen interaction with polar and nonpolar GaAs surfaces. Physical Review B, 2003, 67, .	3.2	11
69	A new horizon in secondary neutral mass spectrometry: post-ionization using a VUV free electron laser. Applied Surface Science, 2004, 231-232, 962-966.	6.1	11
70	A New Insight into Coating TM s Formation Mechanism Between TiO ₂ and Alendronate on Titanium Dental Implant. Materials, 2020, 13, 3220.	2.9	11
71	Electron stimulated desorption of positive and negative ions from surfaces. Nuclear Instruments & Methods in Physics Research B, 1993, 78, 333-336.	1.4	10
72	SIMS and depth profiling of semiconductor structures. Nuclear Instruments & Methods in Physics Research B, 1994, 85, 363-369.	1.4	10

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73	Growth of Zn δ -doped Al _x Ga _{1-x} As by low pressure metal organic vapor phase epitaxy. Journal of Applied Physics, 1995, 78, 3546-3548.	2.5	10
74	Electron stimulated desorption of negative and positive hydrogen ions from hydrogenated silicon surfaces. Physical Review B, 1996, 53, 6996-6998.	3.2	10
75	Oxidation of silicon by low energy oxygen ions. Nuclear Instruments & Methods in Physics Research B, 1997, 121, 24-29.	1.4	10
76	Selective Photon-Stimulated Desorption of Hydrogen from GaAs Surfaces. Physical Review Letters, 2000, 84, 2255-2258.	7.8	10
77	Direct Observation of Defect Levels in InN by Soft X-ray Absorption Spectroscopy. Journal of Physical Chemistry B, 2006, 110, 2984-2987.	2.6	10
78	Electronic structure of nitinol surfaces oxidized by low-energy ion bombardment. Journal of Applied Physics, 2014, 115, .	2.5	10
79	Magnetic oxygen stored in quasi-1D form within BaAl ₂ O ₄ lattice. Scientific Reports, 2019, 9, 15158.	3.3	10
80	Humates and Chlorides Synergistically Increase Cd Phytoaccumulation in Strawberry Fruits, Heightening Health Risk from Cd in Human Diet. Exposure and Health, 2022, 14, 393-410.	4.9	10
81	Hall-effect of the high T _c superconductors Y _{1-x} Ba _x Cu _{1-y} O and Gd _{1-x} Ba _x Cu _{1-y} O. Solid State Communications, 1988, 65, 1355-1358.	1.9	9
82	Isotope effects for mega-electron-volt boron ions in amorphous silicon. Journal of Applied Physics, 1993, 73, 4836-4840.	2.5	9
83	Desorption of positive and negative ions from SiO ₂ /Si surfaces by electron excitation of core levels. Physical Review B, 1993, 48, 2627-2631.	3.2	9
84	On the migration behavior of metal impurities in Si during secondary ion mass spectrometry profiling using low-energy oxygen ions. Journal of Applied Physics, 1999, 85, 3993-3998.	2.5	9
85	Interaction of low-energy nitrogen ions with GaAs surfaces. Journal of Applied Physics, 2008, 104, 063527.	2.5	9
86	Tailoring polypyrrole supercapacitive properties by intercalation of graphene oxide within the layer. Electrochimica Acta, 2016, 193, 311-320.	5.2	9
87	Ge quantum dot lattices in alumina prepared by nitrogen assisted deposition: Structure and photoelectric conversion efficiency. Solar Energy Materials and Solar Cells, 2020, 218, 110722.	6.2	9
88	Initial Stages of Oxide Formation on Copper Surfaces during Oxygen Bombardment at Room Temperature. Journal of Physical Chemistry C, 2021, 125, 25290-25297.	3.1	9
89	Hall effect of the charge-density-wave system (NbSe ₄) ₁₀ /3I. Physical Review B, 1989, 40, 2885-2888.	3.2	8
90	Surface recession and oxidation of silicon during bombardment by low energy oxygen ions. Journal of Applied Physics, 1994, 76, 3831-3834.	2.5	8

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91	Desorption of positive and negative fluorine ions from BaF ₂ surfaces by core level excitation under electron bombardment. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1995, 13, 26-29.	2.1	8
92	Modification of molybdenum surface by low-energy oxygen implantation at room temperature. <i>Applied Surface Science</i> , 2017, 425, 416-422.	6.1	8
93	Molecular layer deposition of hybrid siloxane thin films by ring opening of cyclic trisiloxane (V ₃ D ₃) and azasilane. <i>Chemical Communications</i> , 2020, 56, 8778-8781.	4.1	8
94	Hall effect measurements in La _{2-x} Sr _x CuO ₄ . <i>Solid State Communications</i> , 1988, 65, 573-576.	1.9	7
95	Analysis of semiconductors by ion channelling: Applications and pitfalls. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1998, 136-138, 453-459.	1.4	7
96	SIMS analysis of epitaxial layers for power- and micro-electronics. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1998, 136-138, 1034-1039.	1.4	7
97	On the nitridation of silicon by low energy nitrogen bombardment. <i>Applied Physics Letters</i> , 1998, 73, 1287-1289.	3.3	7
98	Boron doping of silicon layers grown by liquid phase epitaxy. <i>Journal of Crystal Growth</i> , 2002, 241, 45-50.	1.5	7
99	Radical-triggered cross-linking for molecular layer deposition of SiAlCOH hybrid thin films. <i>Chemical Communications</i> , 2021, 57, 2160-2163.	4.1	7
100	On the segregation of metals during low-energy oxygen bombardment of silicon. <i>Applied Surface Science</i> , 1998, 135, 200-204.	6.1	6
101	Electrical characterization of p-GaAs epilayers disordered by doped spin-on-glass. <i>Journal of Applied Physics</i> , 2005, 97, 033524.	2.5	6
102	Effect of Rapid Thermal Annealing on the Atomic Intermixing of Zn- and C-Doped InGaAs/AlGaAs Quantum Well Laser Structures. <i>Journal of the Electrochemical Society</i> , 2006, 153, G879.	2.9	6
103	Electronic Structure and Redox Behavior of Tin Sulfide Films Potentiostatically Formed on Tin. <i>Journal of the Electrochemical Society</i> , 2017, 164, C383-C389.	2.9	6
104	High-pressure study of a charge-density-wave compound (NbSe ₄) _{10/3} . <i>Physical Review B</i> , 1989, 40, 8064-8067.	3.2	5
105	Electron-stimulated desorption of positive and negative oxygen ions from YBa ₂ Cu ₃ O ₇ surfaces. <i>Journal of Applied Physics</i> , 1995, 78, 6858-6860.	2.5	5
106	On the segregation of Ca at SiO ₂ /Si interface during oxygen ion bombardment. <i>Surface and Interface Analysis</i> , 2000, 29, 160-167.	1.8	5
107	Point defects in gallium nitride: X-ray absorption measurements and multiple scattering simulations. <i>Applied Physics Letters</i> , 2011, 99, 172107.	3.3	5
108	η-TaON thin films: production by reactive magnetron sputtering and the question of non-stoichiometry. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 305304.	2.8	5

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109	Electrical transients in the ion-beam-induced nitridation of silicon. Applied Physics Letters, 2001, 78, 3445-3447.	3.3	4
110	Defect Evolution in Hydrogen Implanted Silicon. , 1996, , 832-836.		4
111	Enhanced Oxidation of Nickel at Room Temperature by Low-energy Oxygen Implantation. Croatica Chemica Acta, 2017, 90, .	0.4	4
112	Grain-Size-Induced Collapse of Variable Range Hopping and Promotion of Ferromagnetism in Manganite La _{0.5} Ca _{0.5} MnO ₃ . Crystals, 2022, 12, 724.	2.2	4
113	Core ionization and ion ejection during SIMS analysis. Nuclear Instruments & Methods in Physics Research B, 1992, 64, 659-662.	1.4	3
114	Microstructure of Irradiated Silicon. Materials Research Society Symposia Proceedings, 1994, 373, 543.	0.1	3
115	Electrical activation of carbon δ -doped (Al,Ga)As grown by metalorganic vapour-phase epitaxy. Journal of Crystal Growth, 1997, 173, 302-306.	1.5	3
116	Pulsed anodic oxidation of GaAs for impurity-free interdiffusion of GaAs/AlGaAs quantum wells. Surface and Interface Analysis, 2000, 29, 754-760.	1.8	3
117	Nitrogen defect levels in InN: XANES study. Radiation Physics and Chemistry, 2006, 75, 1635-1637.	2.8	3
118	Vibronic fine structure in high-resolution x-ray absorption spectra from ion-bombarded boron nitride nanotubes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 031405.	2.1	3
119	Prevention of spontaneous combustion of cellulose with a thin protective Al ₂ O ₃ coating formed by atomic layer deposition. Surface and Coatings Technology, 2018, 333, 81-86.	4.8	3
120	Biocompatible Silicon-Based Hybrid Nanolayers for Functionalization of Complex Surface Morphologies. ACS Applied Nano Materials, 2022, 5, 2762-2768.	5.0	3
121	The influence of implanted impurities on the thermally-induced epitaxial recrystallization of CoSi ₂ . Journal of Materials Research, 1991, 6, 1035-1039.	2.6	2
122	Precipitation and segregation of Sb at Si-SiO ₂ interfaces during thermal oxidation. Nuclear Instruments & Methods in Physics Research B, 1992, 64, 156-159.	1.4	2
123	The Influence of Cavities and Point Defects on Cu Gettering and B ⁺ Diffusion in Si. Materials Research Society Symposia Proceedings, 1997, 469, 457.	0.1	2
124	Substrate orientation effect on Zn δ -doping in GaAs grown by metal organic vapour-phase epitaxy. Journal of Crystal Growth, 1998, 191, 357-360.	1.5	2
125	Characterization of Low-Temperature PECVD Silicon Dioxide Films. Materials Research Society Symposia Proceedings, 1998, 555, 197.	0.1	2
126	Efficiency of dislocations and cavities for gettering of Cu and Fe in silicon. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 154-158.	1.4	2

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127	Low energy O ₂ ⁺ and N ₂ ⁺ beam-induced profile broadening effects in Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 893-898.	2.1	2
128	Near-edge X-ray absorption fine-structure studies of GaN under low-energy nitrogen ion bombardment. Applied Surface Science, 2006, 252, 3413-3416.	6.1	2
129	Characterisation of molecular nitrogen in ion-bombarded compound semiconductors by synchrotron-based absorption and emission spectroscopies. Vacuum, 2009, 84, 37-40.	3.5	2
130	Ta ₂ N ₃ nanocrystals grown in Al ₂ O ₃ thin layers. Beilstein Journal of Nanotechnology, 2017, 8, 2162-2170.	2.8	2
131	Structural Behavior and Spin-State Features of BaAl ₂ O ₄ Scaled through Tuned Co ³⁺ Doping. Inorganic Chemistry, 2021, 60, 8475-8488.	4.0	2
132	Oxidation of molybdenum by low-energy oxygen-ion bombardment. Materiali in Tehnologije, 2017, 51, 617-621.	0.5	2
133	Pressure-induced and flaring photocatalytic diversity of ZnO particles hallmarked by finely tuned pathways. Journal of Alloys and Compounds, 2022, 894, 162444.	5.5	2
134	Gettering of metals to nanocavities in silicon. , 0, , .		1
135	Radiation-Induced Segregation of Metals At Moving SiO ₂ -Amorphous Si Interfaces. Materials Research Society Symposia Proceedings, 1996, 439, 575.	0.1	1
136	Perturbed Angular Correlation Measurements and Lattice Site Location of Br in GaAs. Materials Science Forum, 1997, 258-263, 899-904.	0.3	1
137	Evidence for the influence of thermal spikes on ion induced mixing in Si at energies between 3 and 300 keV. Journal of Applied Physics, 1998, 84, 4809-4814.	2.5	1
138	Depth resolution during sputter profiling of Si in GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 85, 388-390.	1.4	0
139	Oxidation-enhanced roughening of thin Co films during sputtering by O ₂ ⁺ ions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 2192-2201.	2.1	0
140	Oxide and Nitride Formation and Segregation of Metals During Oxygen and Nitrogen Bombardment of Silicon. Materials Research Society Symposia Proceedings, 1997, 504, 153.	0.1	0
141	Interactions of Point Defects and Impurities With Open Volume Defects in Silicon. Materials Research Society Symposia Proceedings, 2000, 647, 1.	0.1	0
142	Characterisation of nitrogen-related defects in compound semiconductors by near-edge x-ray absorption fine structure. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
143	Decoration of nitrogen vacancies by oxygen atoms in boron nitride nanotubes. , 2010, , .		0
144	Hydrogen in ZnO: X-ray absorption measurements and multiple scattering theory. , 2014, , .		0

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145	Characterisation of III?V Multilayers Grown by Low-pressure Metal Organic Vapour-phase Epitaxy. Australian Journal of Physics, 1993, 46, 435.	0.6	0
146	GaAs delta-doped layers in Si for evaluation of SIMS depth resolution GaAs. Surface and Interface Analysis, 2000, 29, 362-368.	1.8	0